

# 2SB0710 (2SB710), 2SB0710A (2SB710A)

## Silicon PNP epitaxial planar type

For general amplification

Complementary to 2SD0602 (2SD602), 2SD0602A (2SD602A)

### ■ Features

- Large collector current  $I_C$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0710 $V_{CBO}$	-30	V
	2SB0710A	-60	
Collector-emitter voltage (Base open)	2SB0710 $V_{CEO}$	-25	V
	2SB0710A	-50	
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-0.5	A
Peak collector current	$I_{CP}$	-1	A
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SB0710 $V_{CBO}$	$I_C = -10\text{ }\mu\text{A}$ , $I_E = 0$	-30			V
	2SB0710A		-60			
Collector-emitter voltage (Base open)	2SB0710 $V_{CEO}$	$I_C = -10\text{ mA}$ , $I_B = 0$	-25			V
	2SB0710A		-50			
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10\text{ }\mu\text{A}$ , $I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -20\text{ V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
Forward current transfer ratio *1	$h_{FE1}$ *2	$V_{CE} = -10\text{ V}$ , $I_C = -150\text{ mA}$	85		340	—
	$h_{FE2}$	$V_{CE} = -10\text{ V}$ , $I_C = -500\text{ mA}$	40			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -300\text{ mA}$ , $I_B = -30\text{ mA}$		-0.35	-0.60	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -300\text{ mA}$ , $I_B = -30\text{ mA}$		-1.1	-1.5	V
Transition frequency	$f_T$	$V_{CB} = -10\text{ V}$ , $I_E = 50\text{ mA}$ , $f = 200\text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$		6	15	pF

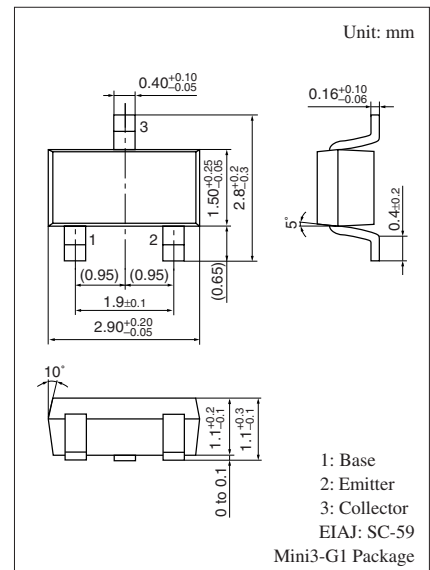
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

\*2: Rank classification

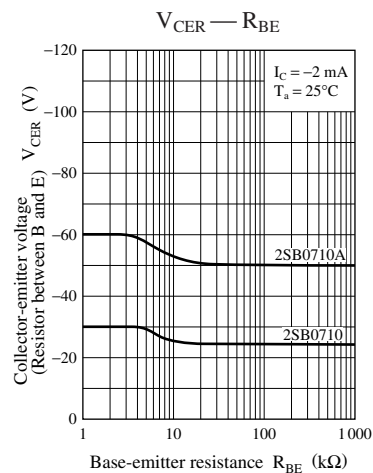
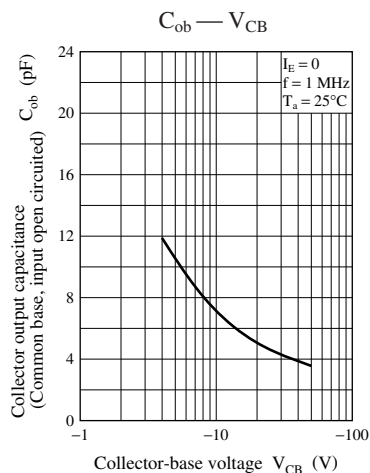
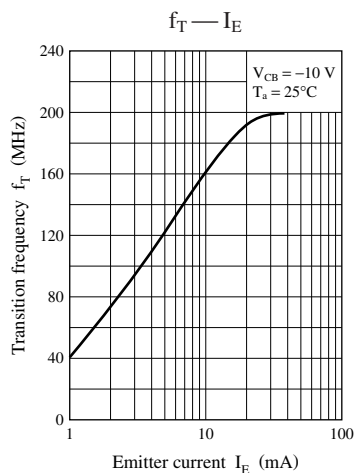
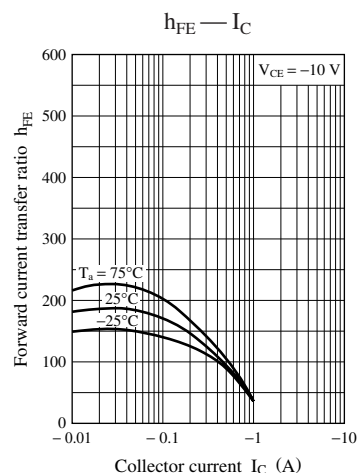
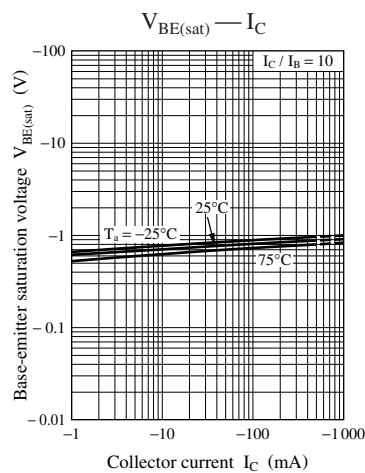
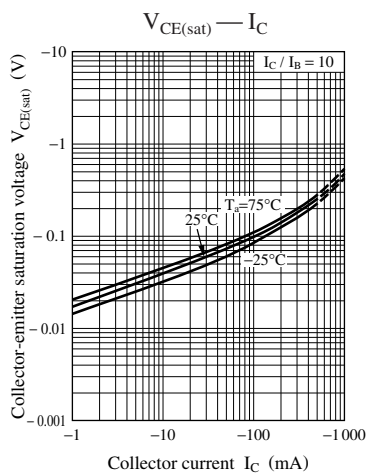
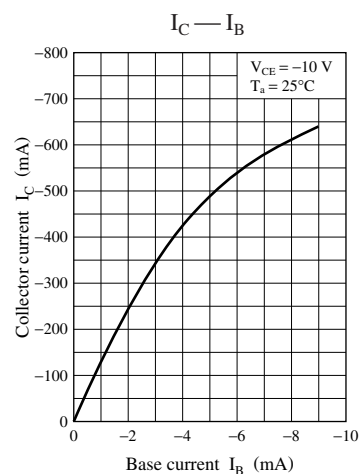
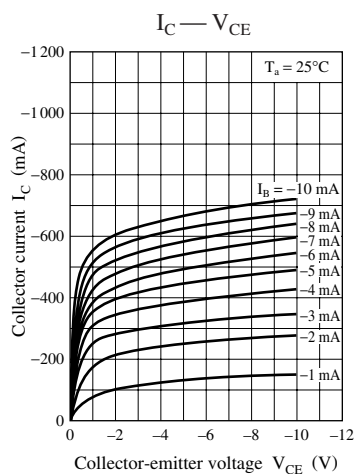
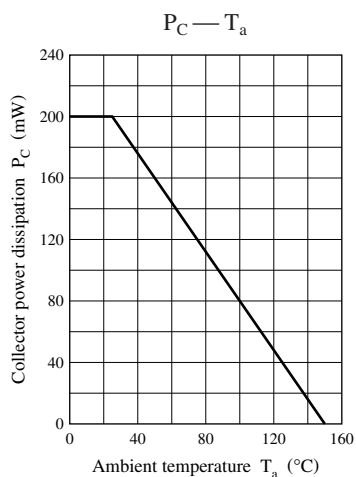
Rank	Q	R	S	No-rank
$h_{FE1}$	85 to 170	120 to 240	170 to 340	85 to 340
Marking symbol	2SB0710	CQ	CR	CS
	2SB0710A	DQ	DR	DS

Note) The part numbers in the parenthesis show conventional part number.



Marking Symbol:

- 2SB0710: C
- 2SB0710A: D



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